

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20050046781").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/13 10:01
S2	200	349/161.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 15:24
S3	173	349/161.ccls. and heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:18
S4	90	S3 and cool\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 10:49
S5	13	S4 and hermetic\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 10:50
S6	1	S5 and hydrophilic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 10:50
S7	122	heat adj interruption	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:20
S8	5	S7 and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:32

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S9	14	heat adj interruption same (circuit semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:31
S10	3	("20030098944").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 14:05
S11	1687	"349"/\$.ccls. and insulat\$4 same heat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:33
S12	0	"349"/\$.ccls. and insulat\$4 same heat\$3 same on same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:33
S13	1055	"349"/\$.ccls. and insulat\$4 same heat\$3 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:33
S14	383	"349"/\$.ccls. and insulat\$4 same heat\$3 same (over on above top resting lying cover covering) same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:40
S15	23919	insulat\$4 same heat\$3 same (over on above top resting lying cover covering) same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:35
S16	2574	S15 and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:35

## EAST Search History

S17	169	"349"/\$.ccls. and insulat\$4 same heat\$3 same (over on above top resting lying cover covering) same substrate same (tft circuit thin adj film semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 13:52
S18	184	"349"/\$.ccls. and insulat\$4 same heat\$3 same surface same substrate same (tft circuit thin adj film semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 15:39
S19	8	349/161.ccls. and substrate same (groove hole gap crack aperture opening cavity) same cool\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 15:30
S20	9	349/8,9.ccls. and substrate same (groove hole gap crack aperture opening cavity) same cool\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 15:41
S21	2	("4975347").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 15:33
S22	2	("5105265").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 15:39
S23	16408	substrate same (groove hole gap crack aperture opening cavity) same cool\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 15:42
S24	391	substrate same (groove hole gap crack aperture opening cavity) same cool\$3 same liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 20:54

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S25	391	substrate same (groove hole gap crack aperture opening cavity) same cool\$3 same liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 20:54
S26	74	S25 and projector	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 20:55
S27	2	("4975347").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 14:05
S28	4749	"349"/\$.ccls. and black adj matrix	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 14:48
S29	229	S28 and cooling	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 14:13
S30	2750	"349"/\$.ccls. and black adj matrix same (block semiconductor TFT thin adj film adj transistor electron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 14:50
S31	427	"349"/\$.ccls. and black adj matrix same (protect shield block) same (semiconductor TFT thin adj film adj transistor electron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 14:50
S32	3	("6618112").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/10 15:45

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S33	1790	349/158,160,161.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 15:45
S34	12	("20010055076" "6340999" "6379017" "6456279" "6507378" "6592234").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 11:17
S35	6	S34 and polariz\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:07
S36	2	S35 and mirror	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:09
S37	2	S36 and (transparent transmissive transmission)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:13
S38	2	S36 and (transparent transmissive transmission) same (reflectance reflection reflector)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:22
S39	2	("6788358").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/13 10:28
S40	0	S34 and prismic adj len	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:29

## EAST Search History

S41	4	S34 and prism	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:31
S42	1	"349"/\$.ccls. and prismic adj lens	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:31
S43	79	"349"/\$.ccls. and prism adj lens	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 10:32
S44	2	("20050200772").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/13 11:37
S45	3	S34 and anti	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/13 11:37